L	Hits	Search Text	DB	Time stamp
Number		a design the standard many viction	USPAT;	2004/10/12
1	237	<pre>plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) same ion near2 beam same (si or silicon)</pre>	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	11:10
3	19	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 ion near2 beam near10 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:11
2	93	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 ion near2 beam same (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:13
4	93	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 (si or silicon) same (ion near2 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:37
5	50	(plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) or PECVD) near10 (si or silicon) same ion near2 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:20
6	0	5795385.pn. and silane same (hydrogen or "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:21
7	1	5795385.pn. and (hydrogen or "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/12
8	592	(kirimura near2 hiroya or kiyoshi near2 ogata).in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:24
9	26	((kirimura near2 hiroya or kiyoshi near2 ogata).in.) and (silicon or si) near2 (film or layer) same (laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12
10	9	((kirimura near2 hiroya or kiyoshi near2 ogata).in.) and (silicon or si) near2 (film or layer) same energy near2 beam	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12
-	2	laser same recrystal\$8 same (silicon or si) near10 crystal\$7 same deposit\$5 same in\$1situ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05
-	4	laser same recrystal\$8 same (silicon or si) near10 crystal\$7 same deposit\$5 same chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05
-	15	laser same recrystal\$8 same (silicon or si) same deposit\$5 same chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05 13:47
-	2	"20010032589"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05 14:07

Search History 10/12/04 1:41:55 PM

	J 5	W0650200W	USPAT;	2004/10/05
-) °	"0652308"	US-PGPUB;	13:52
			EPO; JPO;	13.32
			DERWENT;	
		H.C. 0.2.00 H	IBM_TDB	2004/10/05
_	9	"652308"	USPAT;	2004/10/05
	1		US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
<u> </u>			IBM_TDB	0004/10/05
_	41	laser same deposit\$5 near10 (si or	USPAT;	2004/10/05
		silicon) same in\$1situ	US-PGPUB;	13:57
			EPO; JPO;	
			DERWENT;	
}			IBM_TDB	
-	106	y	USPAT;	2004/10/05
		laser same deposit\$5	US-PGPUB;	14:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	10087	laser near5 (anneal\$5 or recrystal\$8)	USPAT;	2004/10/05
		_	US-PGPUB;	14:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1 _	4493	(laser near5 (anneal\$5 or recrystal\$8))	USPAT;	2004/10/05
	1	same (si or silicon) near5 (film or	US-PGPUB;	14:37
		layer)	EPO; JPO;	
		1 1 0 1 7	DERWENT;	
			IBM TDB	
l <u>_</u>	290	((laser near5 (anneal\$5 or recrystal\$8))	USPAT;	2004/10/05
	230	same (si or silicon) near5 (film or	US-PGPUB;	14:38
		layer)) and vacuum near2 chamber	EPO; JPO;	1
[Tayor// and Vacadim hearz chamber	DERWENT;	
			IBM TDB	· 1
_	24	((laser near5 (anneal\$5 or recrystal\$8))	USPAT;	2004/10/05
	24	same (si or silicon) near5 (film or	US-PGPUB;	14:45
l		layer)) same vacuum near2 chamber	EPO; JPO;	
		Tayor// Same vacuum Hearz Chamber	DERWENT;	
i			IBM TDB	·
_	25	((laser near5 (anneal\$5 or recrystal\$8))	USPAT;	2004/10/05
1 .	45	((laser hears (annears of recrystalso)) same (si or silicon) nears (film or	US-PGPUB;	15:01
		layer)) same (chamber or reactor) near5	EPO; JPO;	10.01
		Tayer) Same (Chamber of reactor) hears "same"	DERWENT;	
		same	IBM TDB	1
	43	lager rears (appeales on requires 167)	USPAT;	2004/10/05
] -	43	laser near5 (anneal\$5 or recrystal\$7) same (chamber or reactor) near5 "same"	·	15:06
1		same (chamber of reactor) hears "same"	US-PGPUB;	12:00
			EPO; JPO;	
			DERWENT;	
L	L		IBM_TDB	